

<b>SANYO</b>	No. 1854A	<b>2SC3661</b>
		NPN Epitaxial Planar Silicon Transistor High $h_{FE}$ , Low-Frequency General-Purpose Amp Applications

**Applications**

- Low frequency general-purpose amplifiers, drivers, muting circuit

**Features**

- Very small-sized package permitting 2SC3661-used sets to be made smaller, slimmer.
- Adoption of FBET process.
- High DC current gain ( $h_{FE}=800$  to  $3200$ ).
- Low collector-to-emitter saturation voltage ( $V_{CE(sat)} \leq 0.5V$ ).
- High  $V_{EBO}$  ( $V_{EBO} \geq 15V$ ).

**Absolute Maximum Ratings at  $T_a=25^\circ C$**

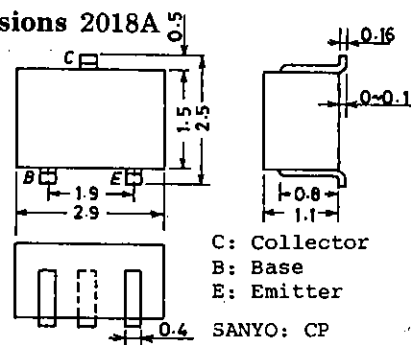
			unit
Collector to Base Voltage	$V_{CBO}$	30	V
Collector to Emitter Voltage	$V_{CEO}$	25	V
Emitter to Base Voltage	$V_{EBO}$	15	V
Collector Current	$I_C$	300	mA
Collector Current(Pulse)	$I_{CP}$	500	mA
Collector Dissipation	$P_C$	200	mW
Junction Temperature	$T_j$	125	$^\circ C$
Storage Temperature	$T_{stg}$	-55 to +125	$^\circ C$

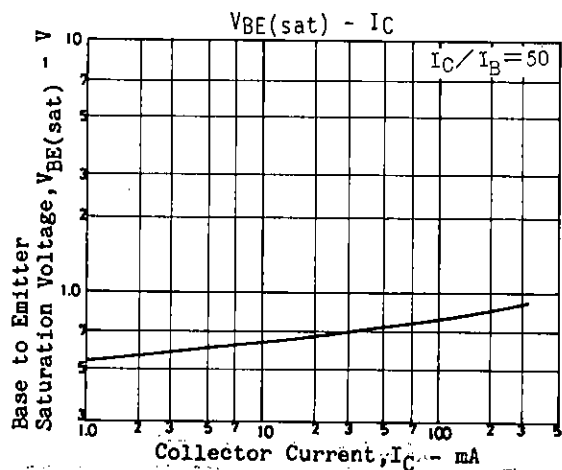
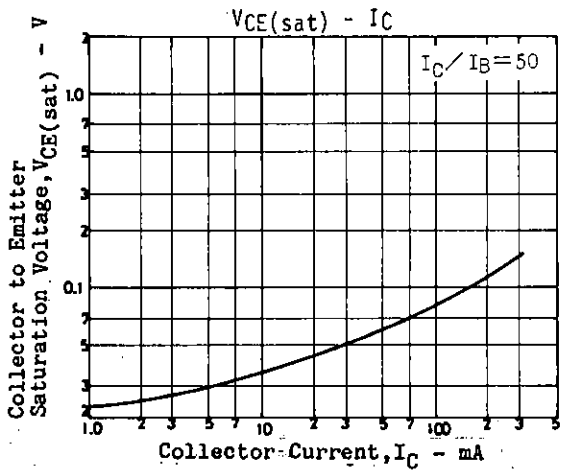
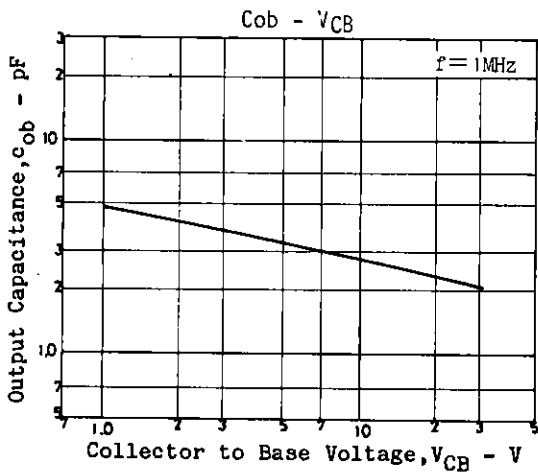
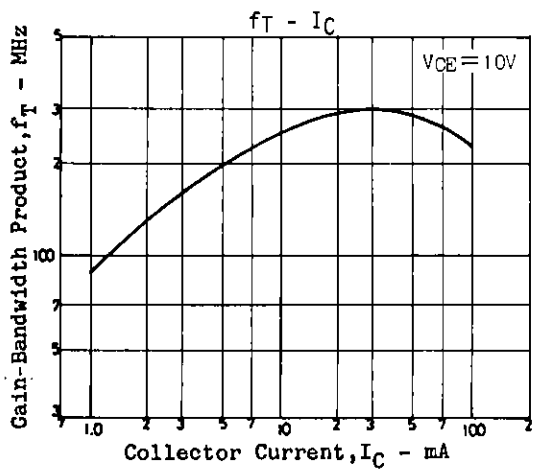
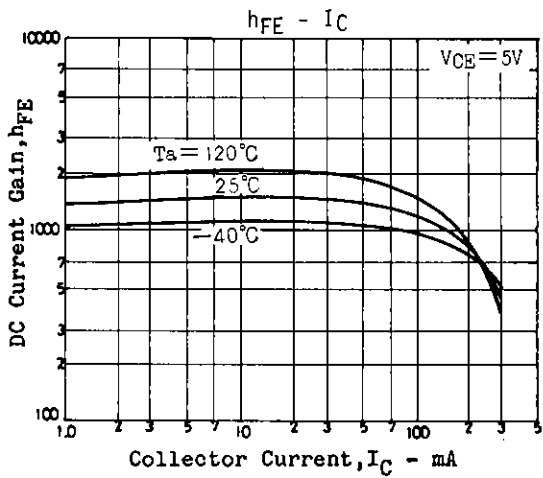
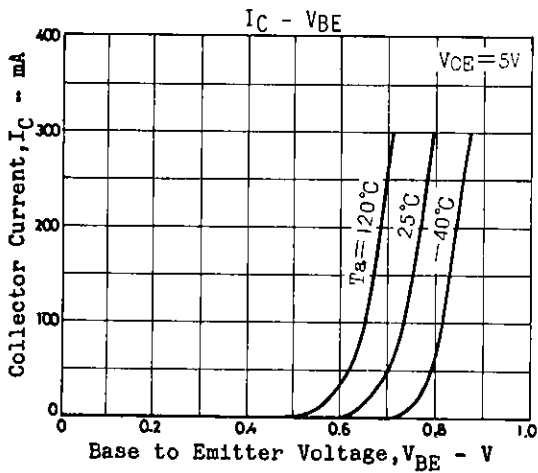
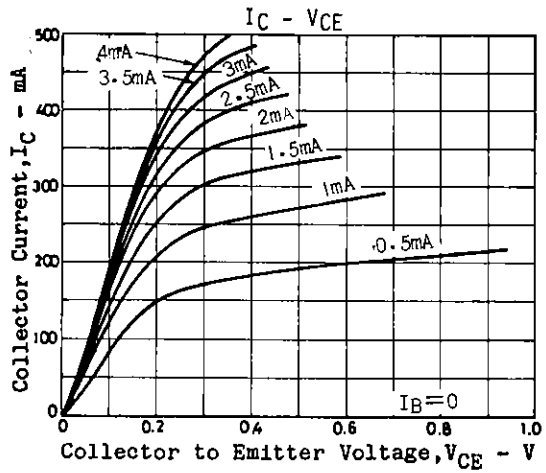
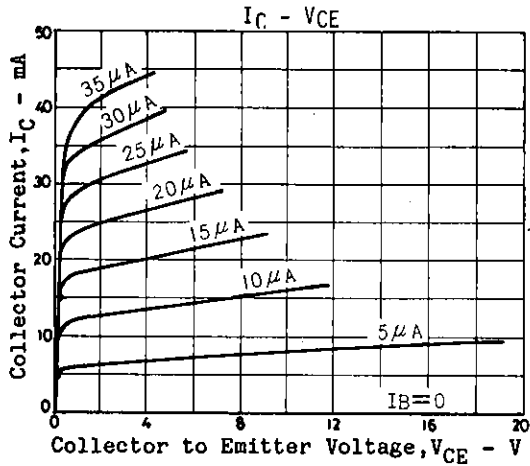
**Electrical Characteristics at  $T_a=25^\circ C$**

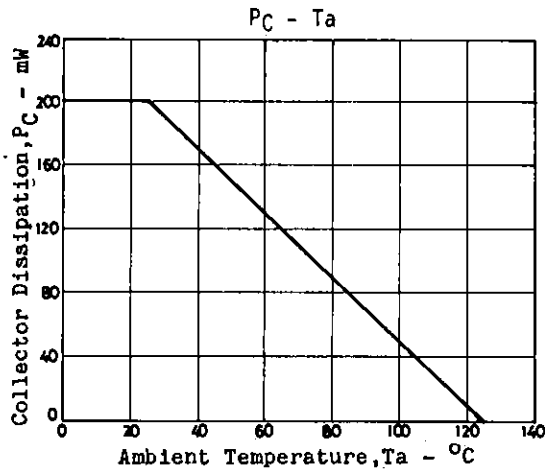
			min	typ	max	unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=20V, I_E=0$			0.1	$\mu A$
Emitter Cutoff Voltage	$I_{EBO}$	$V_{EB}=10V, I_C=0$			0.1	$\mu A$
DC Current Gain	$h_{FE}$	$V_{CE}=5V, I_C=10mA$	800	1500	3200	
Gain-Bandwidth Product	$f_T$	$V_{CE}=10V, I_C=10mA$		250		MHz
Output Capacitance	$c_{ob}$	$V_{CB}=10V, f=1MHz$		2.7		pF
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=200mA, I_B=4mA$	0.12	0.5		V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=200mA, I_E=4mA$	0.85	1.2		V
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	30			V
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	25			V
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	15			V

Marking : FY

**Package Dimensions 2018A**  
(unit:mm)







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